

In re: Allen *et al.*
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Please replace the paragraph at page 22, lines 3-8 with the following amended paragraph:

FIG. 6G illustrates the formation of a Si_3N_4 layer **110** on the wafer. **FIG. [6G] 6H** also illustrates that the substrate **10** may be thinned as described above to provide a thinned substrate **10'**. The metallization **32** may then be formed on the thinned substrate **10'** as illustrated in **FIG. 6I**. Contact holes may also be formed through the Si_3N_4 layer **110** so as to allow contact between the source, drain and gate contacts and a metallized interconnect layer (not shown).